

**Silicon NPN Power Transistors**

**2SC1913 2SC1913A**

**DESCRIPTION**

- With TO-220 package
- Complement to type 2SA913/913A
- Large collector power dissipation
- High  $V_{CEO}$

**APPLICATIONS**

- Audio frequency high power driver

**PINNING**

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

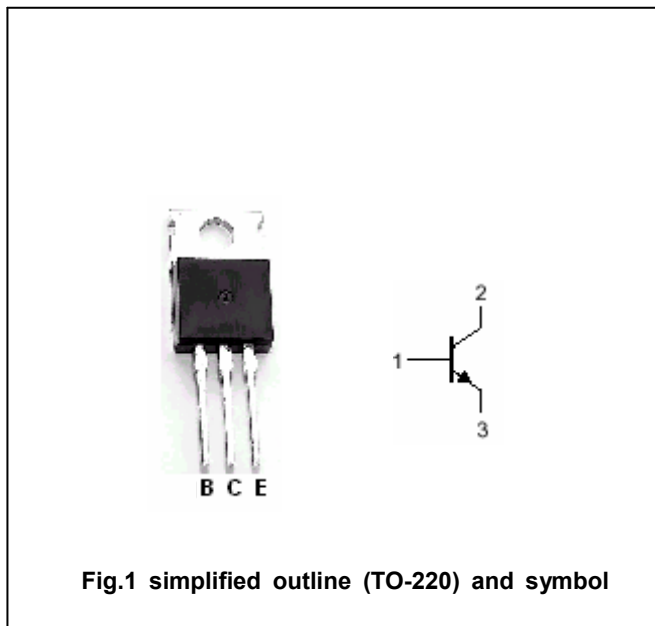


Fig.1 simplified outline (TO-220) and symbol

**Absolute maximum ratings(Ta=25°C)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	2SC1913	150	V
		2SC1913A	180	
$V_{CEO}$	Collector-emitter voltage	2SC1913	150	V
		2SC1913A	180	
$V_{EBO}$	Emitter-base voltage	Open collector	5	V
$I_C$	Collector current		1	A
$I_{CM}$	Collector current-peak		1.5	A
$P_C$	Collector power dissipation	$T_C=25^\circ C$	15	W
$T_j$	Junction temperature		150	°C
$T_{stg}$	Storage temperature		-55~150	°C

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	2SC1913	I <sub>C</sub> =0.1mA, I <sub>B</sub> =0	150			V
		2SC1913A		180			
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage		I <sub>E</sub> =10μA, I <sub>C</sub> =0	5			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	2SC1913	I <sub>C</sub> =0.3A; I <sub>B</sub> =30mA			1.0	V
		2SC1913A				1.5	
V <sub>BEsat</sub>	Base-emitter saturation voltage		I <sub>C</sub> =0.3A; I <sub>B</sub> =30mA			1.5	V
I <sub>CBO</sub>	Collector cut-off current		V <sub>CB</sub> =120V; I <sub>E</sub> =0			1	μA
I <sub>EBO</sub>	Emitter cut-off current		V <sub>EB</sub> =4V; I <sub>C</sub> =0			1	μA
h <sub>FE-1</sub>	DC current gain		I <sub>C</sub> =150mA; V <sub>CE</sub> =10V	65		330	
h <sub>FE-2</sub>	DC current gain		I <sub>C</sub> =500mA; V <sub>CE</sub> =5V	50			
C <sub>OB</sub>	Output capacitance		I <sub>E</sub> =0; V <sub>CB</sub> =100V; f=1MHz			15	pF
f <sub>T</sub>	Transition frequency		I <sub>C</sub> =50mA; V <sub>CE</sub> =10V		120		MHz

◆ h<sub>FE-1</sub> Classifications

P	Q	R	S
65-110	90-155	130-220	185-330

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PACKAGE OUTLINE

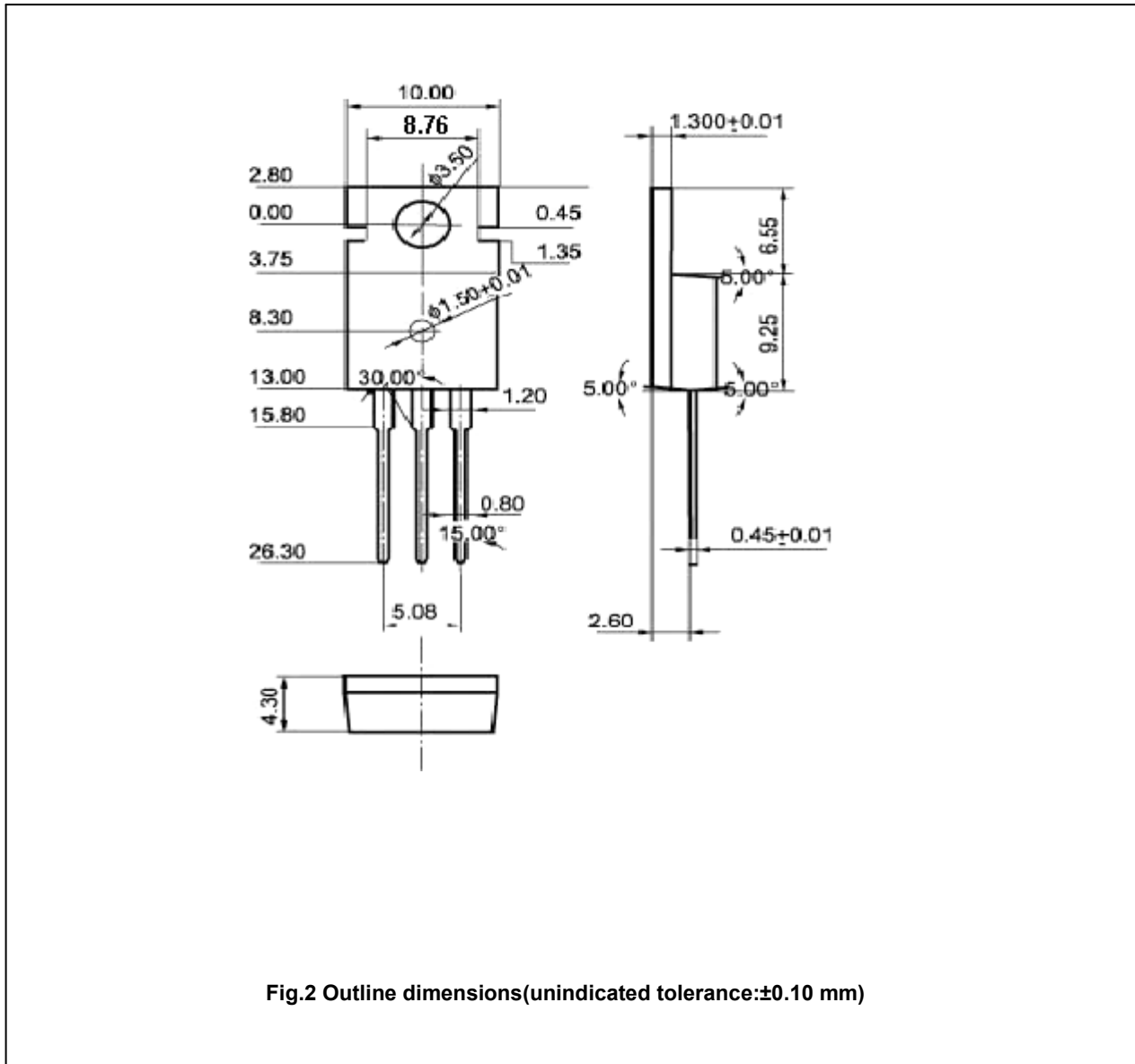


Fig.2 Outline dimensions(unindicated tolerance:±0.10 mm)